P-Channel Enhancement Mode Power MOSFET

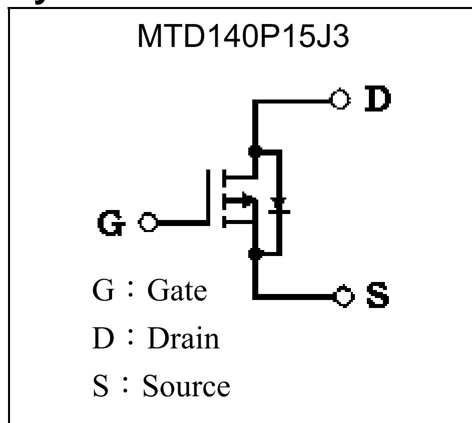
MTD140P15J3

BV_{DSS}	-150V
I_D	-15A
$R_{DS(ON)}$@V_{GS}=-10V, I_D=-12A	141mΩ(typ)
$R_{DS(ON)}$@V_{GS}=-4.5V, I_D=-10A	175mΩ(typ)

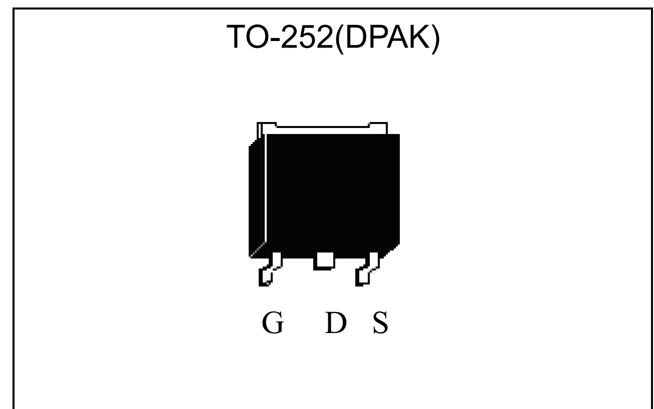
Features

- Single Drive Requirement
- Low On-resistance
- Fast switching Characteristic
- Pb-free lead plating and halogen-free package

Symbol

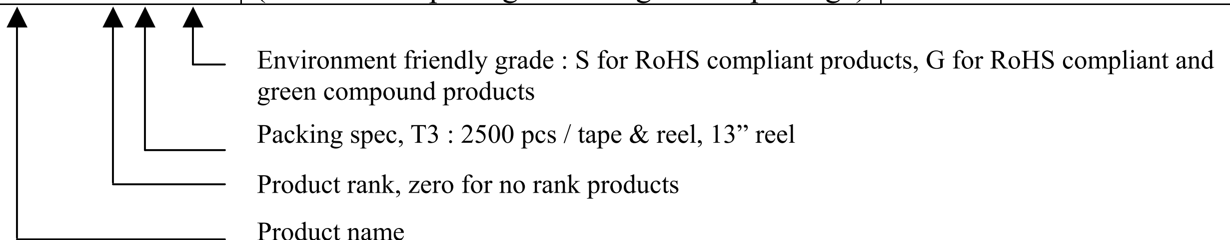


Outline



Ordering Information

Device	Package	Shipping
MTD140P15J3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	-150	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current @V_{GS}=-10V, T_C=25°C (Note1)		I_D	-15	A
Continuous Drain Current @V_{GS}=-10V, T_C=100°C (Note1)			-10.6	
Continuous Drain Current @V_{GS}=-10V, T_A=25°C (Note4)			-2.4	
Continuous Drain Current @V_{GS}=-10V, T_A=70°C (Note4)			-1.9	
Pulsed Drain Current (Note3)		I_{DM}	-60	
Power Dissipation	T_C=25℃ (Note1)	P_D	100	W
	T_C=100℃ (Note1)		50	
	T_A=25℃ (Note2)	P_{DSM}	2	
	T_A=70℃ (Note2)		1.3	
Single Pulse Avalanche Energy		E_{AS}	225	mJ
Single Pulse Avalanche Current		I_{AS}	-15	A
Operating Junction and Storage Temperature		Tj, Tstg	-55~+175	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1.5	°C/W
Thermal Resistance, Junction-to-ambient, max (Note2)	$R_{th,j-a}$	62.5	
Thermal Resistance, Junction-to-ambient, max (Note4)		90	

Note : 1.The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

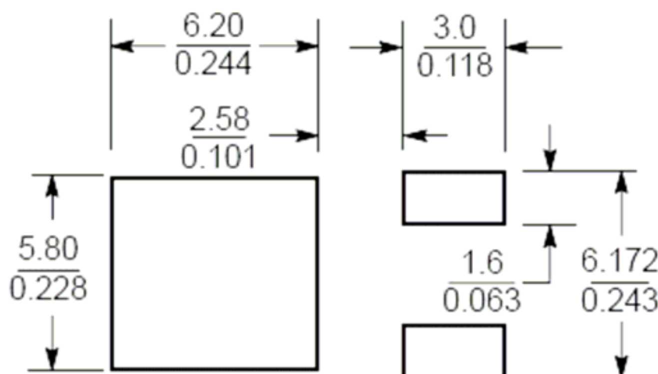
4. When mounted on the minimum pad size recommended (PCB mount), t≤10s.

Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-150	-	-	V	V_{GS}=0V, I_D=-250μA
$\Delta BV_{DSS}/\Delta Tj$	-	-0.12	-	V/°C	Reference to 25°C, I_D=-250μA
$V_{GS(th)}$	-1.0	-2.5	-3.0	V	V_{DS} = V_{GS}, I_D=-250μA
G_{FS}	-	18	-	S	V_{DS} =-5V, I_D=-12A
I_{GSS}	-	-	±100	nA	V_{GS}=±20V
I_{DSS}	-	-	-1	μA	V_{DS} =-120V, V_{GS} =0V
I_{DSS}	-	-	-25		V_{DS} =-120V, V_{GS} =0V, Tj=70°C
*$R_{DS(ON)}$	-	141	185	mΩ	V_{GS} =-10V, I_D=-12A
*$R_{DS(ON)}$	-	175	230		V_{GS} =-4.5V, I_D=-10A
Dynamic					
*Qg	-	51	-	nC	V_{DS}=-120V, I_D=-12A, V_{GS}=-10V
*Qgs	-	11	-		
*Qgd	-	21	-		
*$t_{d(ON)}$	-	14	-	ns	V_{DS}=-75V, V_{GS}=-10V, I_D=-12A , R_G=3.3Ω
*tr	-	16	-		
*$t_{d(OFF)}$	-	37	-		
*t_f	-	24	-		
Ciss	-	2473	-	pF	V_{GS}=0V, V_{DS}=-25V, f=1MHz
Coss	-	122	-		
Crss	-	75	-		
Rg	-	2.9	-	Ω	f=1MHz
Source-Drain Diode					
*V_{SD}	-	-0.84	-1.2	V	I_S=-12A, V_{GS}=0V
*I_S	-	-	-15	A	
*trr	-	70	-	ns	I_S=-12A, V_{GS}=0, dI/dt=-100A/μs
*Qrr	-	245	-	nC	

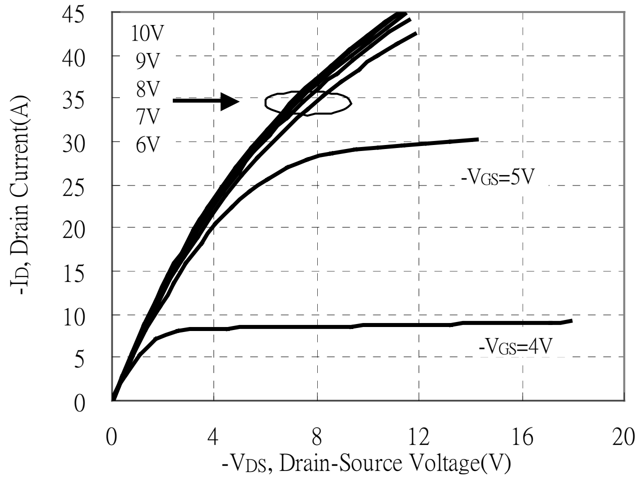
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

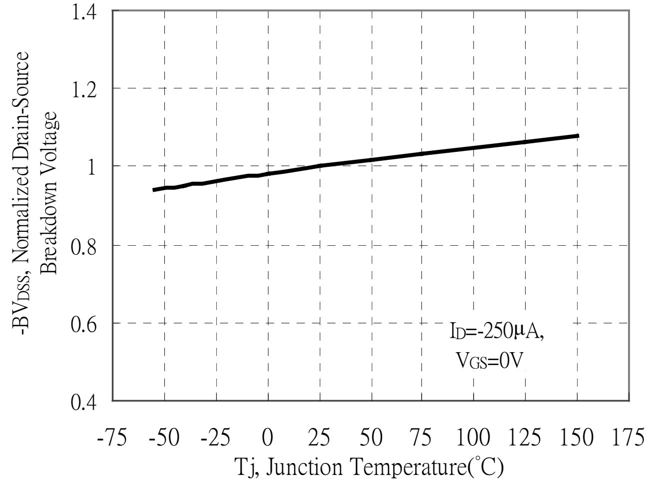
Recommended soldering footprint

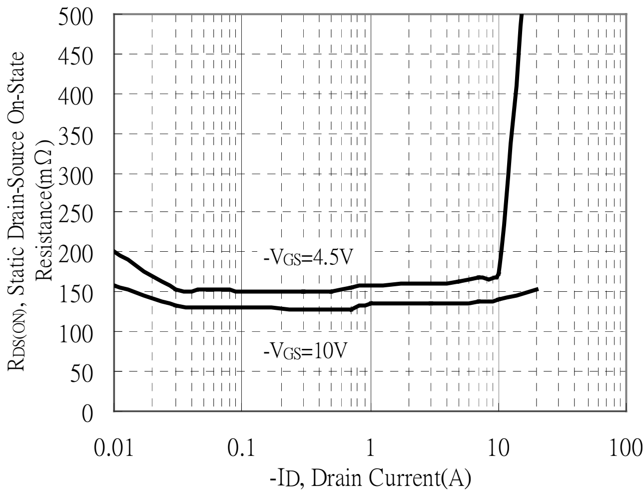


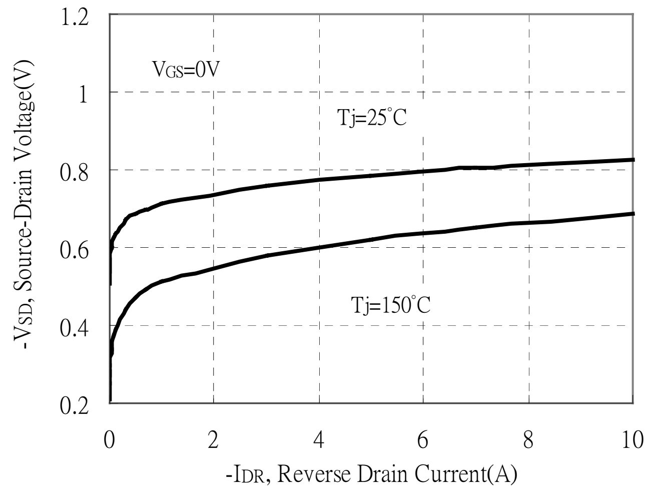
Unit (mm / inch)

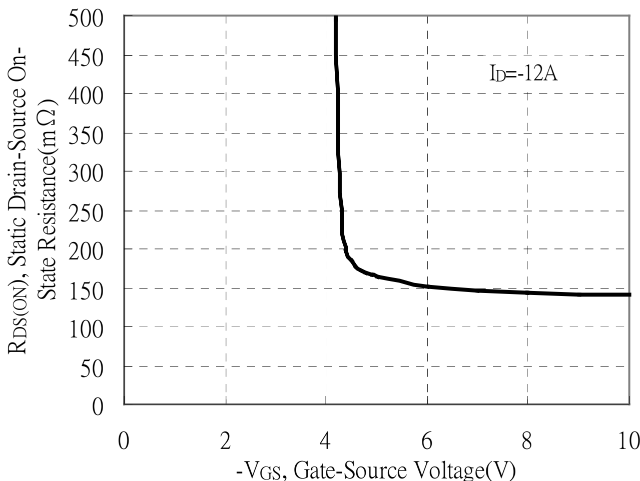
Typical Characteristics

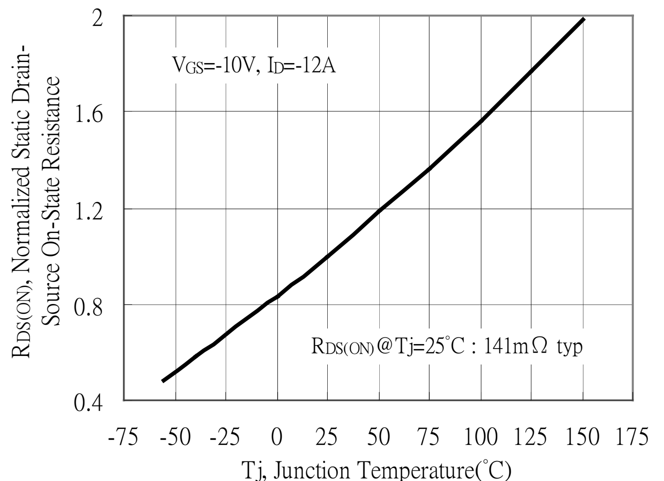




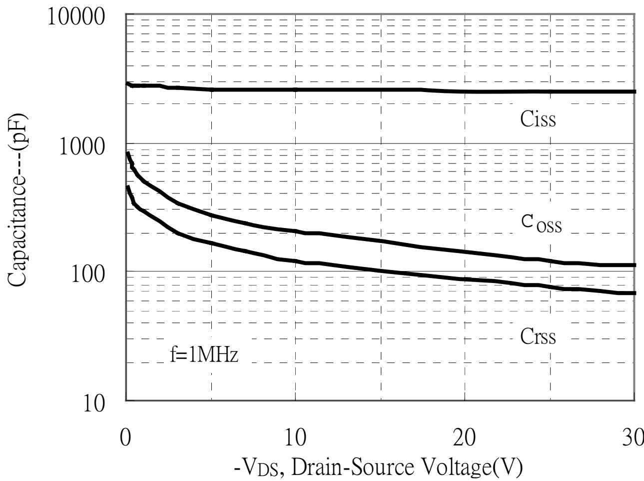


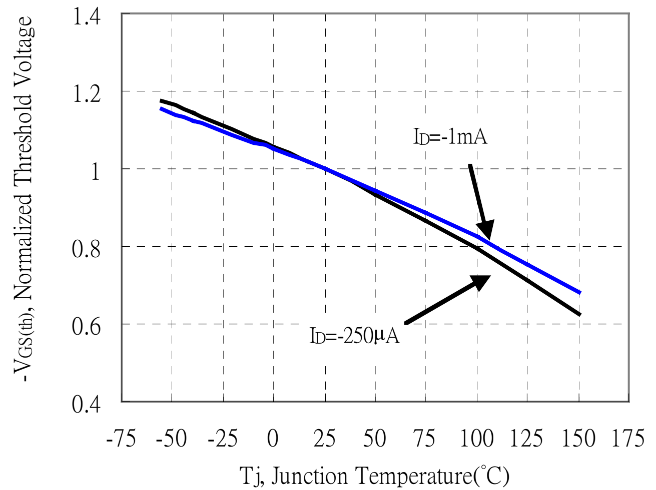


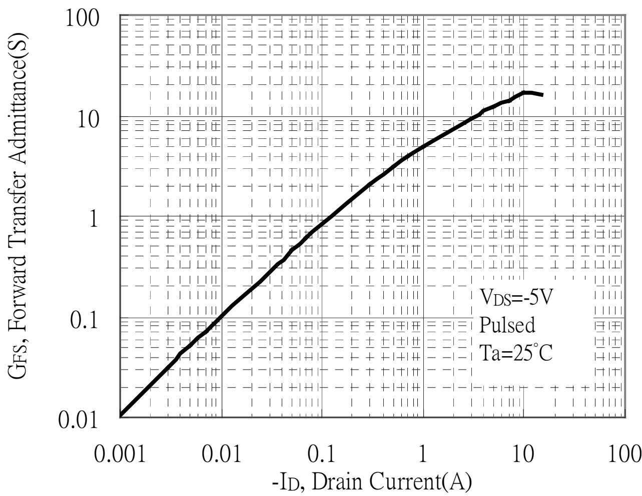


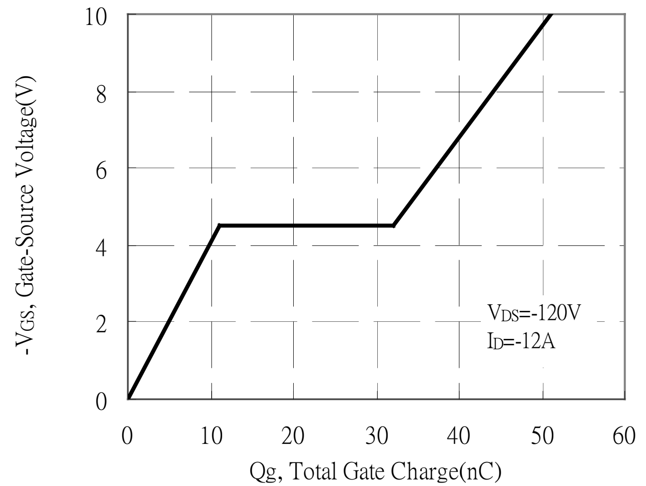


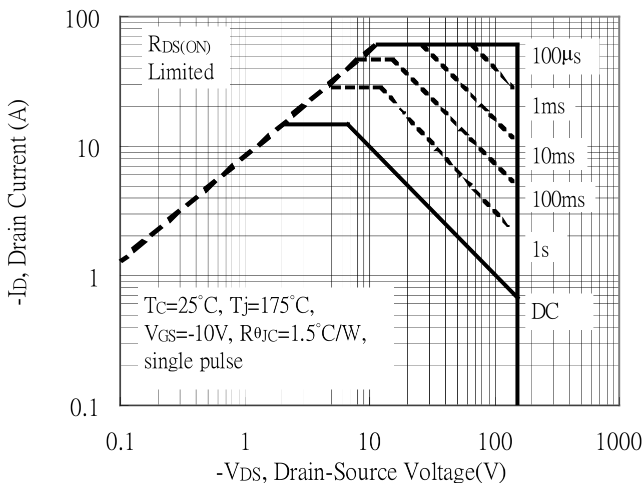
Typical Characteristics(Cont.)

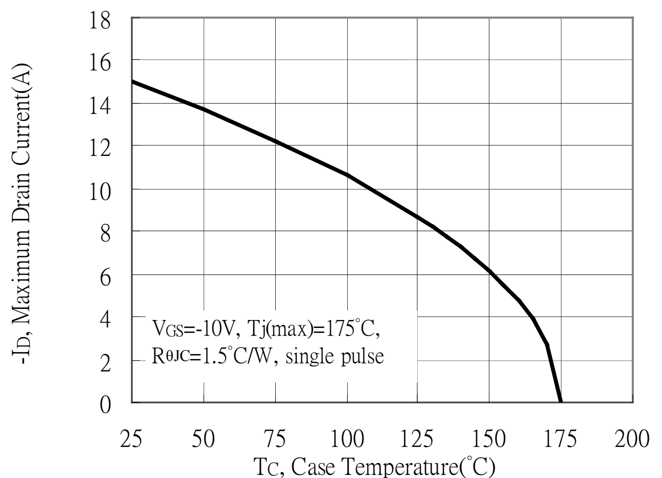




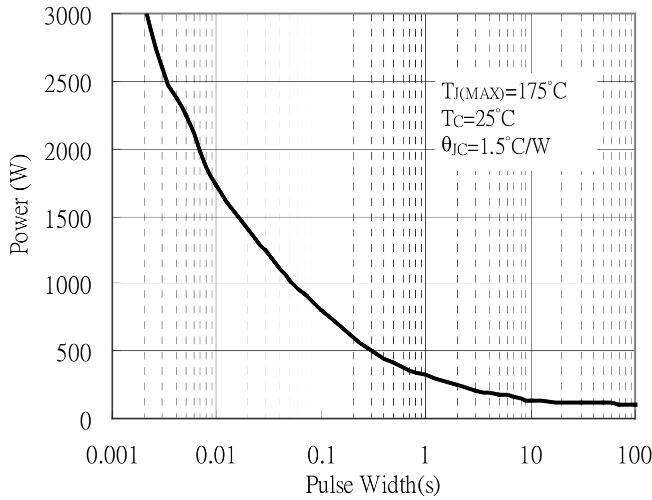


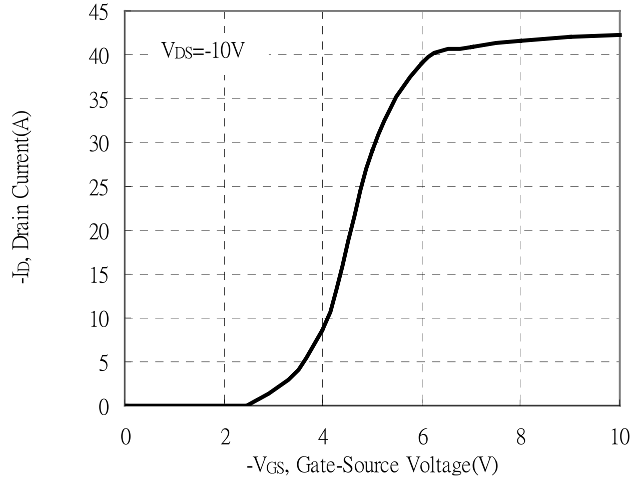


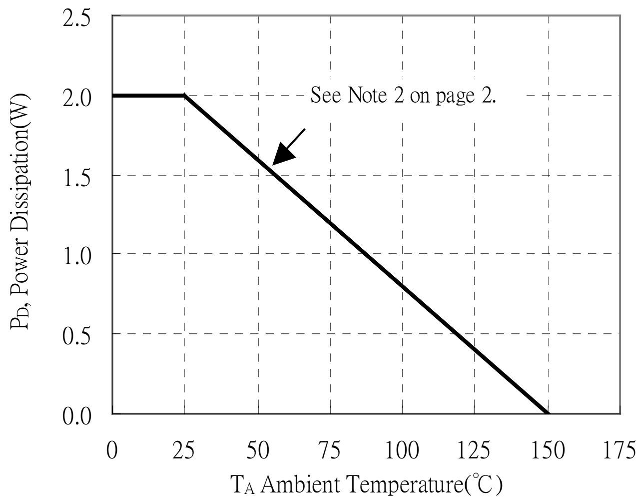


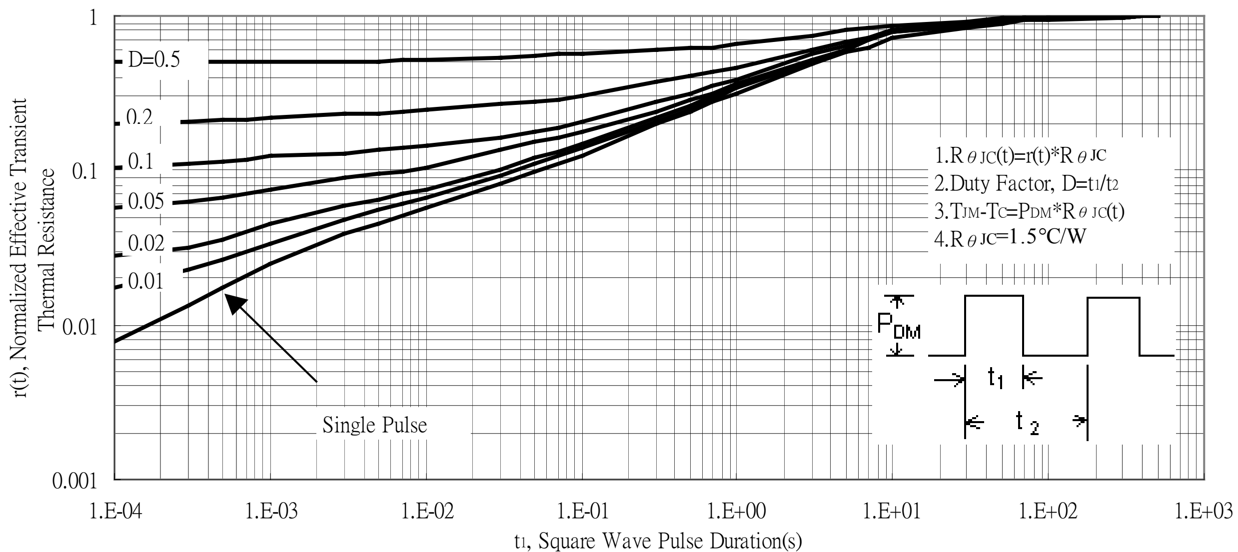


Typical Characteristics(Cont.)

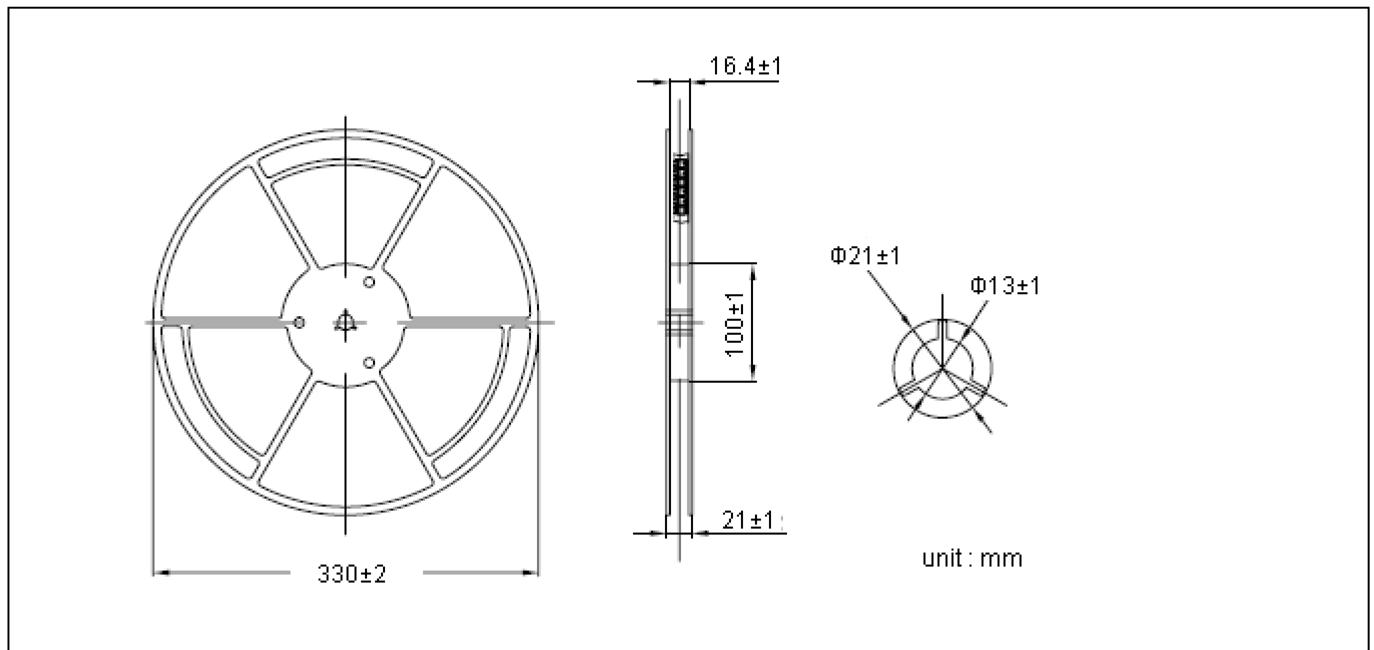




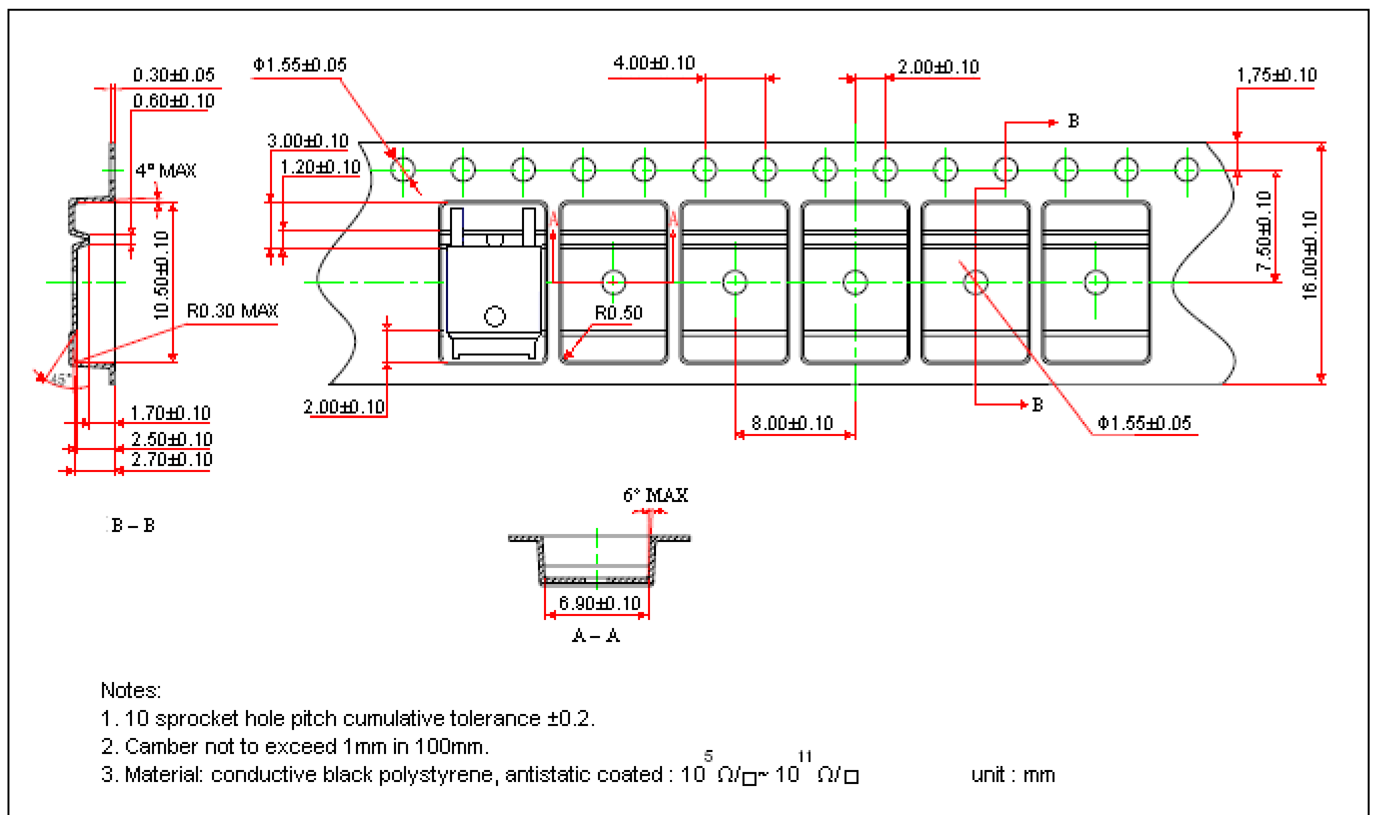




Reel Dimension



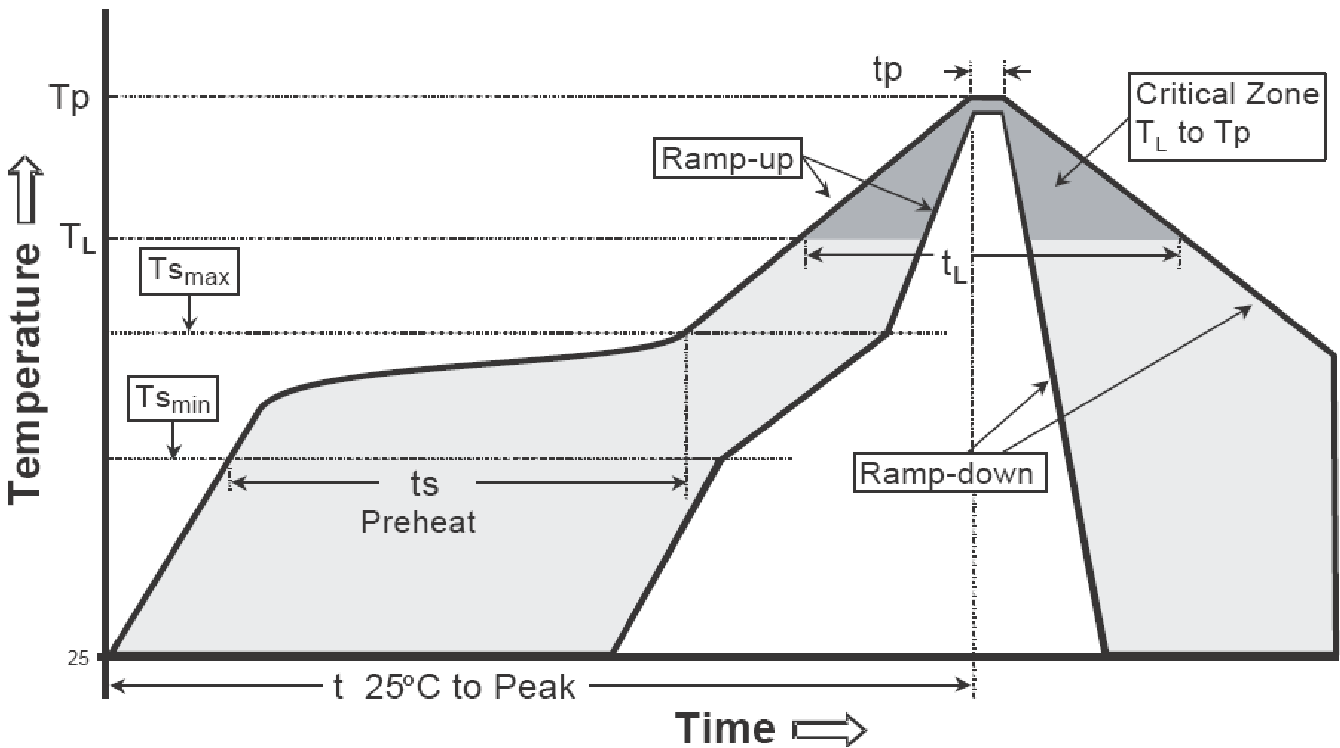
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

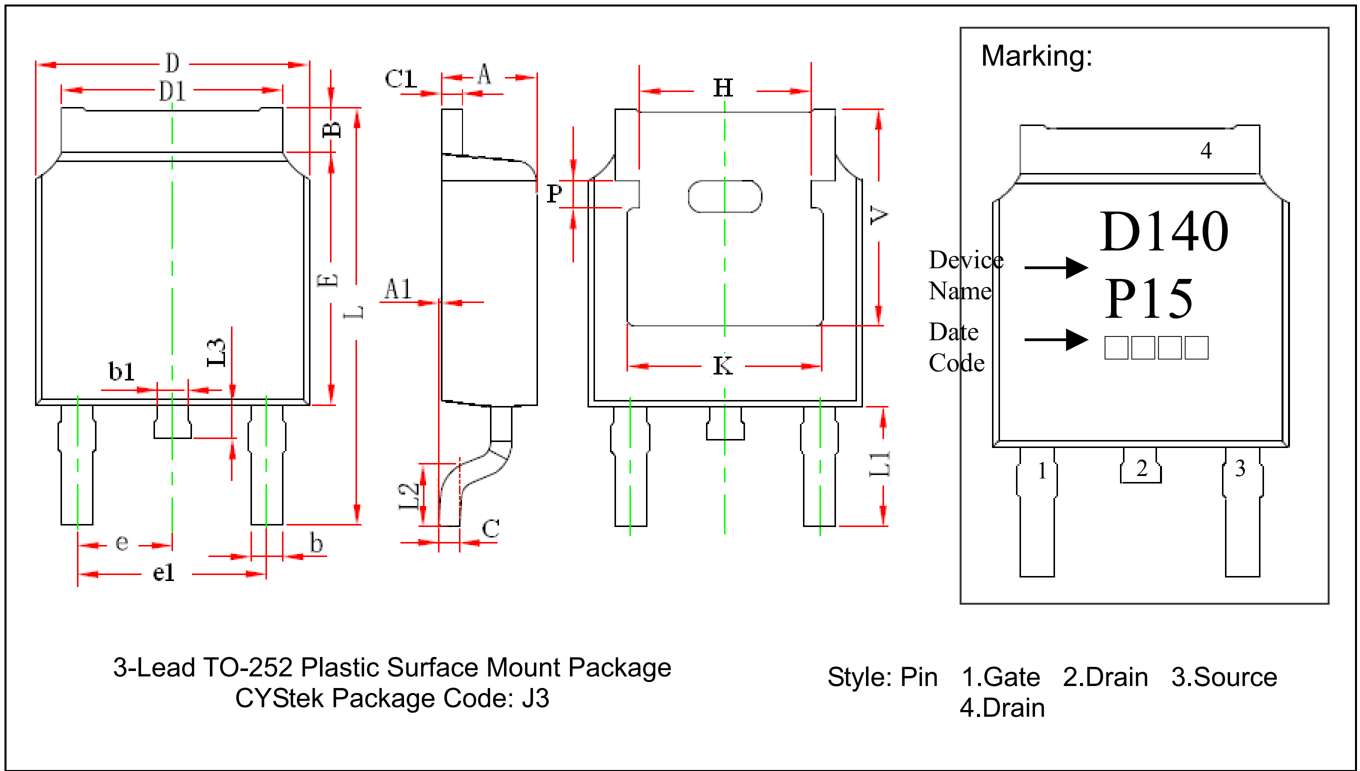
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(Ts min) −Temperature Max(Ts max) −Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package
CYStek Package Code: J3

Style: Pin 1.Gate 2.Drain 3.Source 4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek ***semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.***
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.